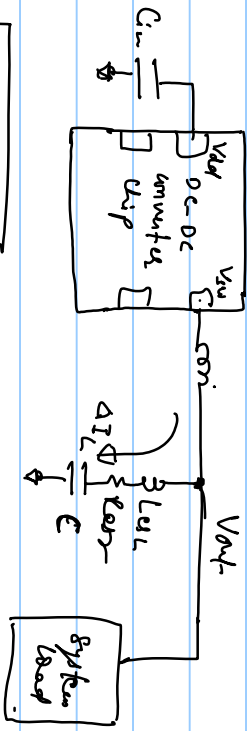
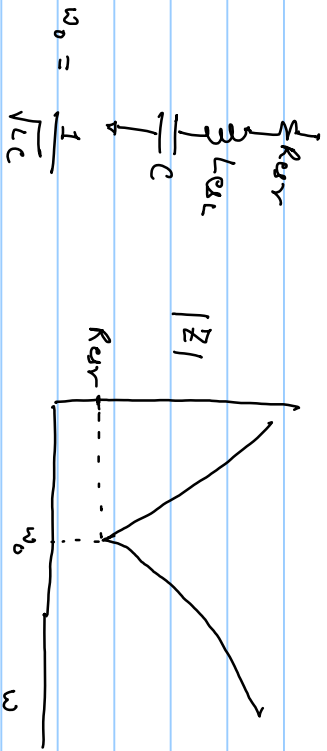


ESL in capacitor.

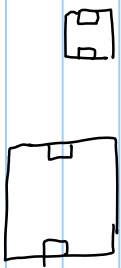
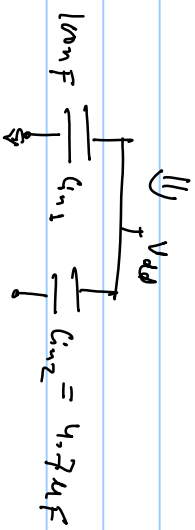


$$V_L = L \frac{di}{dt}$$

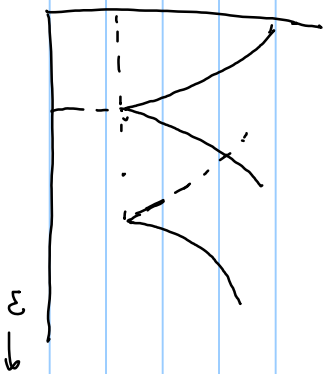
$$L = 1 \mu\text{H}, \quad di = 1\text{A}, \quad dt = 1 \mu\text{s}$$

$$V_L = 1\text{V}$$

V_{dd} \downarrow $C_{in} \Rightarrow$ Add cap to pins closer to V_{dd} pin due to limited space

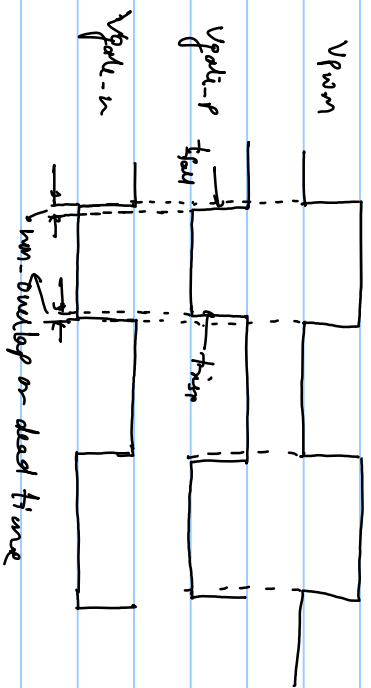
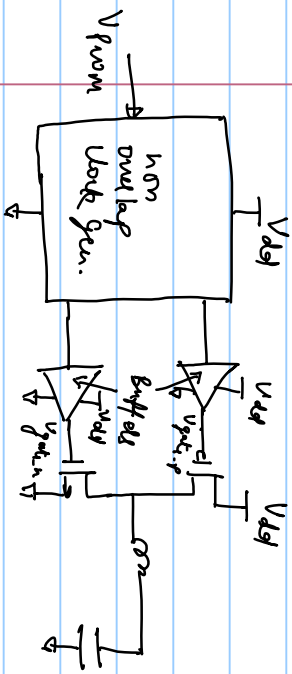


[Z]

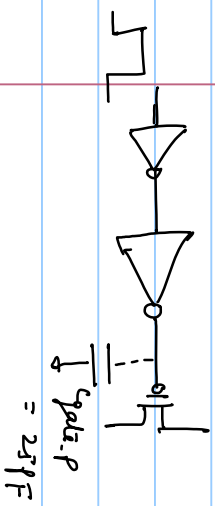


Gate driver circuit-

= nm-overlap volt generator + gate buffers



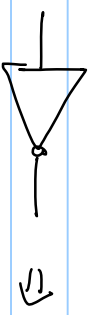
t_{fall} & $t_{rise} \rightarrow 1-2ns$
 $t_{dead} \rightarrow 1-2ns$



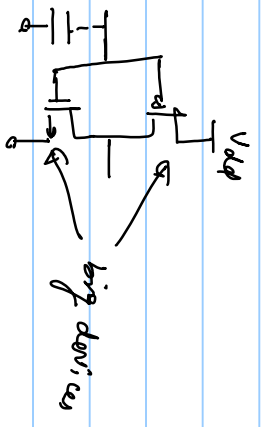
$t_{rise} = t_{gate} = 1 \mu\text{s}$

2 to 3 RC time constant $\approx 1 \mu\text{s}$

$RC \approx 0.5 \mu\text{s}$



\Rightarrow



$RC = R_{on} \times C_{gate.p}$

